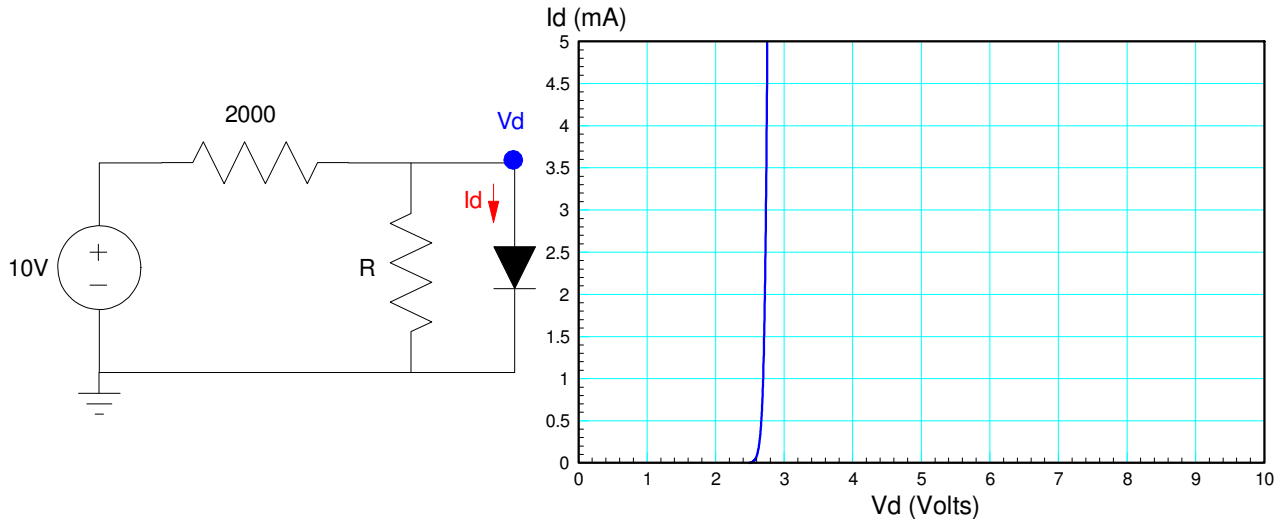


ECE 320 - Final (pt 1) - Name _____

Semiconductors & Diodes - Spring 2023

1) Load Lines: Assume the VI characteristics for the diode is as shown in the graph. Draw the load line for the following circuit and determine I_d and V_d . Assume $R = 800 + 100 * (\text{your birth month}) + (\text{your birth date})$.



R $800 + 100 * \text{mo} + \text{day}$	Load Line x-intercept (volts)	Load Line y-intercept (mA)	V_d Volts	I_d mA

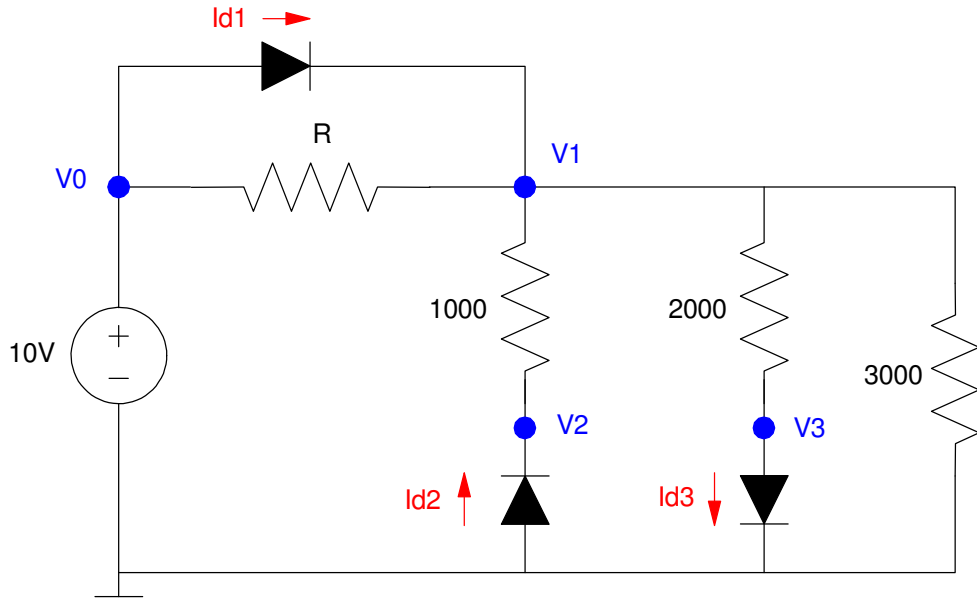
2) Nonlinear equations: Diode circuit

Assume the VI characteristics for the diodes shown below are

$$V_d = 0.038 \ln(10^{11} \cdot I_d + 1) \quad I_d = 10^{-11} \cdot \left($$

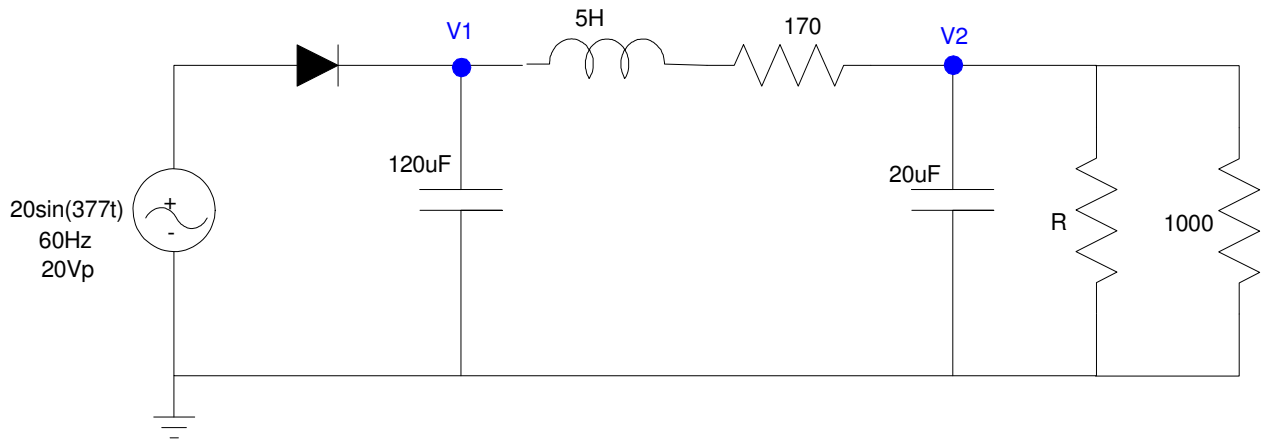
3) Ideal Silicon Diodes. Assume the diodes in this circuit are ideal silicon diodes:

- $V_d = 0.7V$ $I_d > 0$
- $I_d = 0$ $V_d < 0.7V$
- $R = 800 + 100 * (\text{your birth month}) + (\text{birth date})$.



R $800 + 100 * \text{mo} + \text{day}$	I_{d1}	I_{d2}	I_{d3}
V1	V2	V3	V4

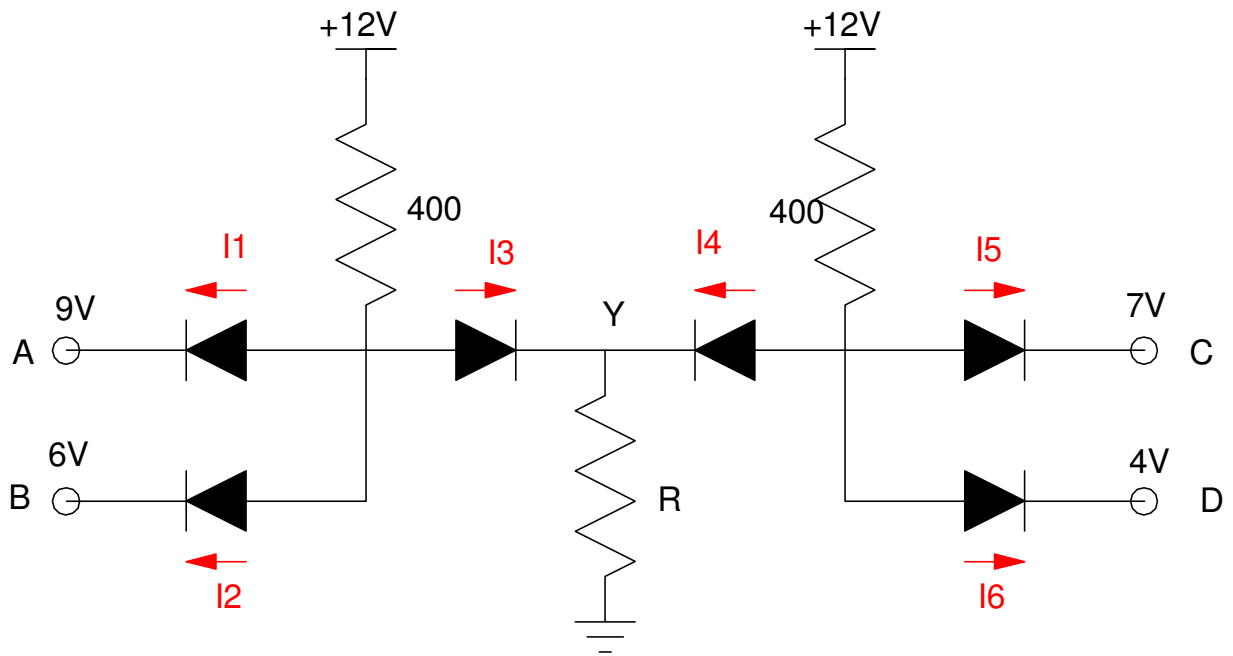
4) AC to DC: Analysis: Determine V1 and V2 (both DC and AC) for the following AC to DC converter



R 800 + 100*mo + day	V1		V2	
	DC	AC	DC	AC

5) Max/Min Circuits. Determine the currents I_1 .. I_6 . Assume

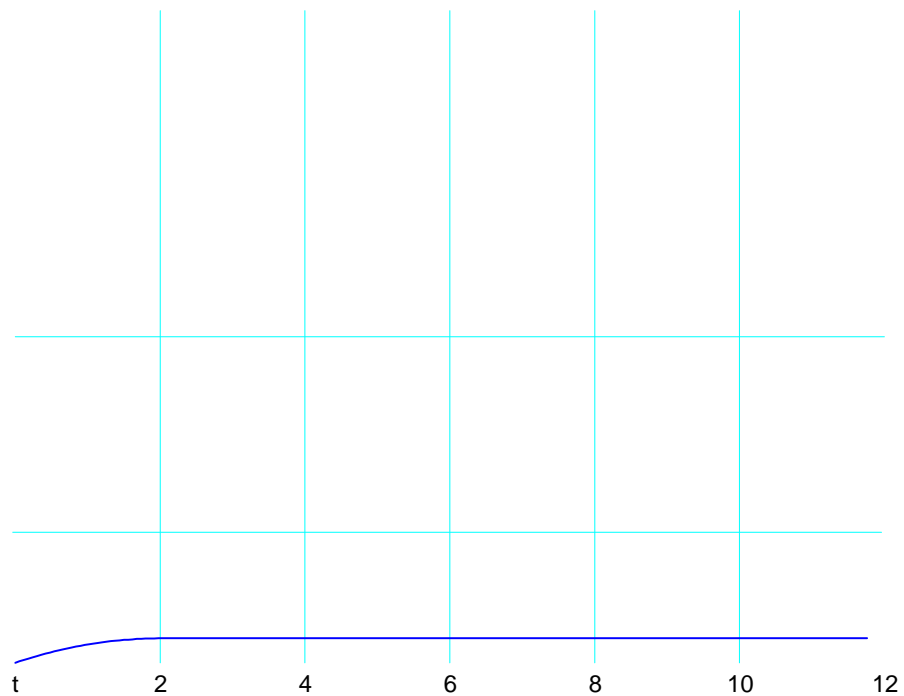
- Ideal silicon diodes ($V_f = 0.7V$)
- $R = 800 + 100 * (\text{your birth month}) + (\text{birth date})$



R $800 + 100 * \text{mo day}$	I_1	I_2	I_3	I_4	I_5	I_6

9) MOSFET Load Line: For the following MOSFET cir

- Determine the transconductance gain, k_n ,
- Draw the load line (x and y intercept), and
- Determine $\{V_{ds}, I_{ds}\}$ when $V_g = 7V$. (note: $V_{th} = 2V$)



10) CMOS Logic

Design a CMOS logic gate to implement $Y=f(A,B,C,D)$

		CD			
		00	01	11	10
AB	00	1	0	1	1
	01	x	0	x	1
	11	1	0	0	x
	10	1	1	0	0